



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. 09/118,359
Filing Date July 17, 1998
Inventor J. Dennis Keller et al.
Assignee Micron Technology, Inc.
Group Art Unit 2823
Examiner M. Estrada
Attorney's Docket No. MI22-587
Title: Methods of Forming Floating Gate Transistors, and Floating Gate Transistors

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT


Reference - - See attached Form PTO-1449

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the references listed on the attached Form PTO-1449. No admission is made regarding whether the submitted references are prior art.

Citation of these references are respectfully requested.

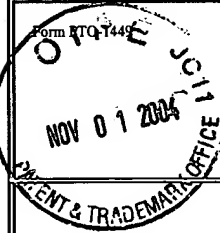
Respectfully submitted,

Date: 11/1/04



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EV372469661

Form TQ-7446 		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-587		SERIAL NO. 09/118,359	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT J. Dennis Keller et al.			
				FILING DATE July 17, 1998		GROUP 2823	

U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AA						
	AB						
	AC						
	AD						
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	AF						
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	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS							
Document Number	Date	Country	Class	Subclass	Translation		
					Yes	No	
AL							
AM							
AN							
AO							
AP							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)		
AR		H. Shirai, et al., A 0.54 μ m ² Self-Aligned, HSG Floating Gate Cell (SAHF Cell) for 256Mbit Flash Memories, 1995 IEEE pp27.1.1-27.1.4
AS		Yosiaki S. Hisamune et al, A High Capacitive-Coupling Ratio (HiCR) Cell for 3 V-Only 64 Mbit and Future Flash Memories, 1993 IEEE pp2.3.1-2.3.4
AT		

EXAMINER	DATE CONSIDERED
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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